EAST - [10644415 finfet with trench capacitor.wsp: 1]

File View Edit Tools Window Help

L8: (79) 7 with 4
L9: (79) 8 with 5
L10: (49) trech
L11: (86948) trench
L12: (1614876) capacit$4
L13: (2) 12 near 10
L14: (8637) 12 near2 11
L15: (8) 14 and 8
L16: (2) "20021118255"
L17: (261) (finfet fin adj2 (fet mosfet mos transistor))
L18: (10) 17 and 14
L19: (10) 18 and 12
L20: (132188) fin
L21: (10) 19 and 20
L22: (89493) (wordline "WL" ((word digit control adj gate) adj line) (word near (read$
L23: (28073) 5 near9 22
L24: (8) 21 and 23
L25: (102356) (bl bitline bit adj line readline read adj line sense adj line)
L26: (6) 24 and 25
L27: (545653) (FOX field adj oxide STI (isolati$3 (element adj (insulat$4 separat$
L28: (6) 26 and 27
L29: (4) ("6316813" "5567962").pn.
L30: (195084) strap$4
L31: (3) 29 and 30
Failed
Saved

Browse Queue Clear

DBs USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Plurals

Default operator: OR

Highlight all hit terms initially

29 and 30

Sept 2004

	U	^1	Inventor	Document I	Issue	P	Title	Current	CurrentXR	Retrieval	S	C	P	2	3	4	5	Image Doc.	P
1			Kondo, Masa	US 2004015	20040	3	Double-gate structure fin-type transistor	257/623										US 200401	
2			Brown, Jeffr	US 2004012	20040	1	DRAM cell with enhanced SER immunity	438/257										US 200401	
3			Brown, Jeffr	US 2004003	20040	1	DRAM cell with enhanced SER immunity	257/296										US 200400	

Ready

NUM